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Application No.10/604,883  
Docket No.: 10766-US-PA**DECLARATION TRAVERSING REJECTIONS UNDER 37 CFR §1.132**

As below named inventors of the subject matter which is claimed and for which a patent is sought on the invention entitled:

**METHOD OF MANUFACTURING A LOW TEMPERATURE POLYSILICON FILM**

The specification of which was filed on August 25, 2003 as Application Serial No.:10/604,883.

We hereby declare that in order to overcome the 35 U.S.C. 112, 1<sup>st</sup> and 2<sup>nd</sup> paragraphs rejections, we provide the following statements and information.

To our knowledge, it is comprehensible to a skilled artisan that "a size of a silicon seed" refers to "the diameter of the silicon seed". In the attached US Patent 6,329,270 to Voutsas, the microcrystallites (seed crystals) 116 are comparable to the silicon seeds of the instant application, and Voutsas discloses that the size of the microcrystallites 116 is associated with "the diameter of the microcrystallites. In column 19, lines 5-6, Voutsas recites "...the size, or diameter of microcrystallites 116 is preferably 1000Å or less".

We hereby declare that all statements made herein of our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful, false statements may jeopardize the validity of the application or any patent issued thereon.

Full Name:

Signature: Chien-Shen Wung Date: September 18, 2006  
Chien-Shen Wung

Signature: Mao-Yi Chang Date: September 18, 2006  
Mao-Yi Chang

Signature: \_\_\_\_\_ Date: \_\_\_\_\_  
Chih-Chin Chang

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**Full Name:**Signature : \_\_\_\_\_ Date : \_\_\_\_\_  
Chien-Shen WungSignature : \_\_\_\_\_ Date : \_\_\_\_\_  
Mao-Yi ChangSignature: Chih-Chin Chang Date : \_\_\_\_\_  
Chih-Chin Chang